

1SS133

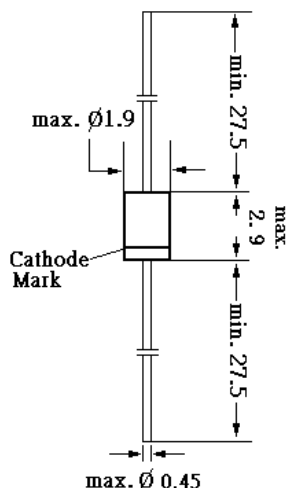
HIGH SPEED SWITCHING DIODE

Features

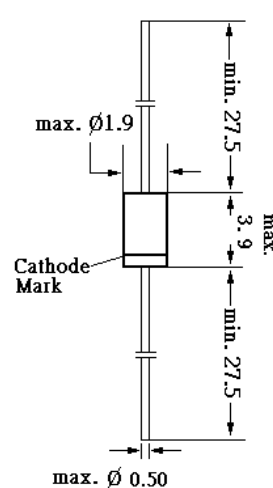
- Glass sealed envelope. (MSD)
- High speed. ($t_{rr} = 1.2\text{ns Typ.}$)
- High reliability.

Construction

- Silicon epitaxial planar.



Glass case JEDEC DO-34
Dimensions in mm



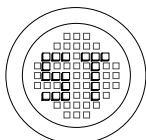
Glass case JEDEC DO-35
Dimensions in mm

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Limits	Unit
Peak Reverse Voltage	V_{RM}	90	V
DC Reverse Voltage	V_R	80	V
Peak Forward Current	I_{FM}	400	mA
Mean Rectifying Current	I_o	130	mA
Surge Current (1s)	I_{surge}	600	mA
Power Dissipation	P_{tot}	300	mW
Junction Temperature	T_j	175	$^\circ\text{C}$
Storage Temperature Range	T_s	-65 to +175	$^\circ\text{C}$

Characteristics at $T_{amb} = 25^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward Voltage	V_F	-	-	1.2	V	$I_F = 100\text{mA}$
Reverse Current	I_R	-	-	0.5	μA	$V_R = 80\text{V}$
Capacitance Between Terminals	C_T	-	-	2	pF	$V_R = 0.5\text{V}, f = 1\text{MHz}$
Reverse Recovery Time	t_{rr}	-	-	4	ns	$V_R = 6\text{V}, I_F = 10\text{mA}, R_L = 50\Omega$



®

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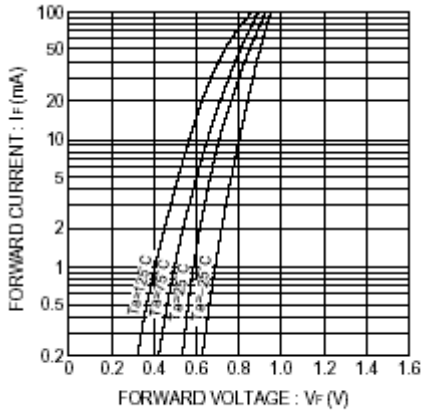


Fig. 1 Forward characteristics

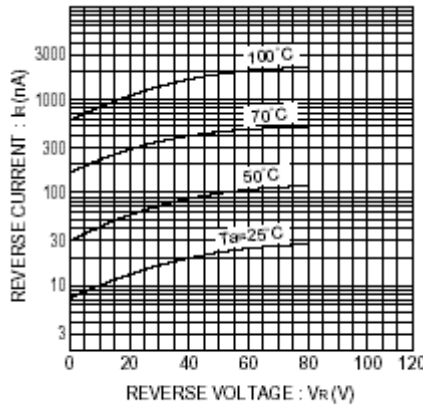


Fig. 2 Reverse characteristics

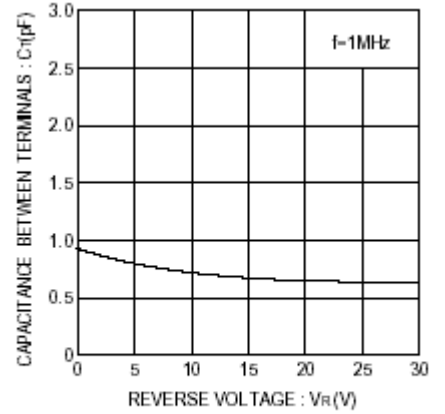


Fig. 3 Capacitance between terminals characteristics

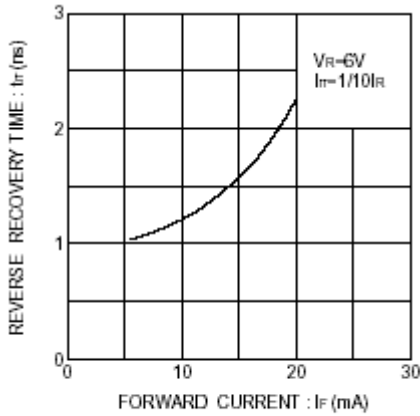


Fig. 4 Reverse recovery time characteristics

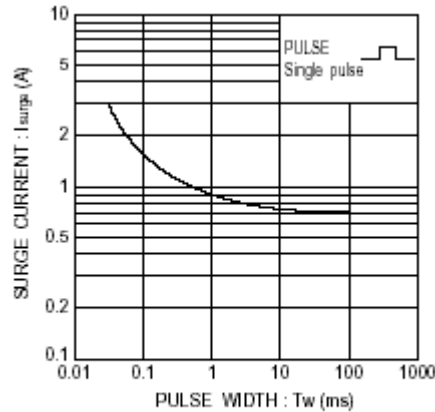


Fig. 5 Surge current characteristics

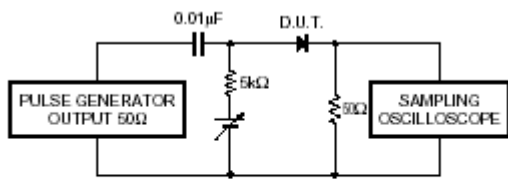
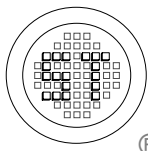


Fig. 6 Reverse recovery time (t_r) measurement circuit



SEMTECH ELECTRONICS LTD.

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